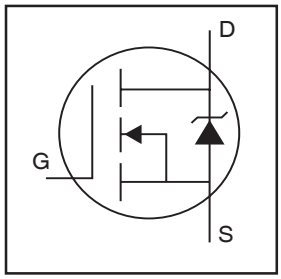
PD-94791B

International
IOR Rectifier

IRF3205PbF

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



V_{DSS} = 55V

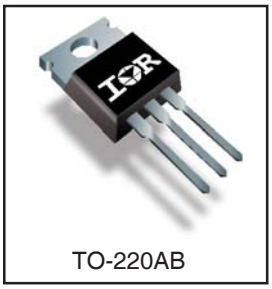
$R_{DS(on)}$ = 8.0mΩ

I_D = 110A⑤

Description

Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



TO-220AB

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	110 ⑤	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	80	
I_{DM}	Pulsed Drain Current ①	390	
P_D @T_C = 25°C	Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
I_{AR}	Avalanche Current①	62	A
E_{AR}	Repetitive Avalanche Energy①	20	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 srew	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.75	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	62	

07/23/10

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.057	—	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	8.0	mΩ	V_{GS} = 10V, I_D = 62A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 250µA
g_{fs}	Forward Transconductance	44	—	—	S	V_{DS} = 25V, I_D = 62A④
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	µA	V_{DS} = 55V, V_{GS} = 0V
		—	—	250		V_{DS} = 44V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -20V
Q_g	Total Gate Charge	—	—	146	nC	I_D = 62A
Q_{gs}	Gate-to-Source Charge	—	—	35		V_{DS} = 44V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	54		V_{GS} = 10V, See Fig. 6 and 13
$t_{d(on)}$	Turn-On Delay Time	—	14	—	ns	V_{DD} = 28V
t_r	Rise Time	—	101	—		I_D = 62A
$t_{d(off)}$	Turn-Off Delay Time	—	50	—		R_G = 4.5Ω
t_f	Fall Time	—	65	—		V_{GS} = 10V, See Fig. 10 ④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	3247	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	781	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	211	—		f = 1.0MHz, See Fig. 5
E_{AS}	Single Pulse Avalanche Energy②	—	1050⑥	264⑦	mJ	I_{AS} = 62A, L = 138µH

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	110	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode)①	—	—	390		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	T_J = 25°C, I_S = 62A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	69	104	ns	T_J = 25°C, I_F = 62A
Q_{rr}	Reverse Recovery Charge	—	143	215	nC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 138µH
R_G = 25Ω, I_{AS} = 62A. (See Figure 12)

③ I_{SD} ≤ 62A, di/dt ≤ 207A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 175°C

④ Pulse width ≤ 400µs; duty cycle ≤ 2%.

⑤ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.

⑥ This is a typical value at device destruction and represents operation outside rated limits.

⑦This is a calculated value limited to T_J = 175°C.

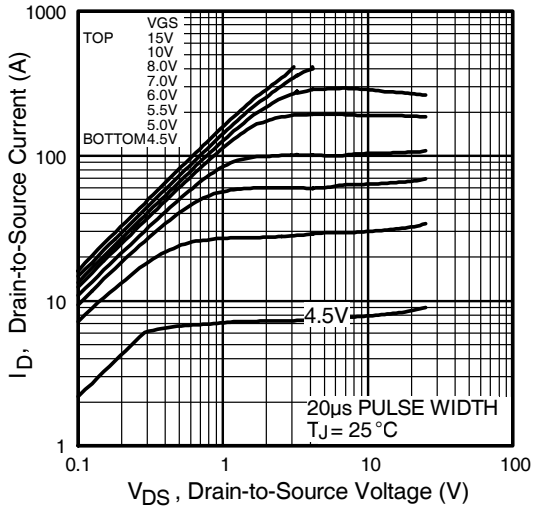


Fig 1. Typical Output Characteristics

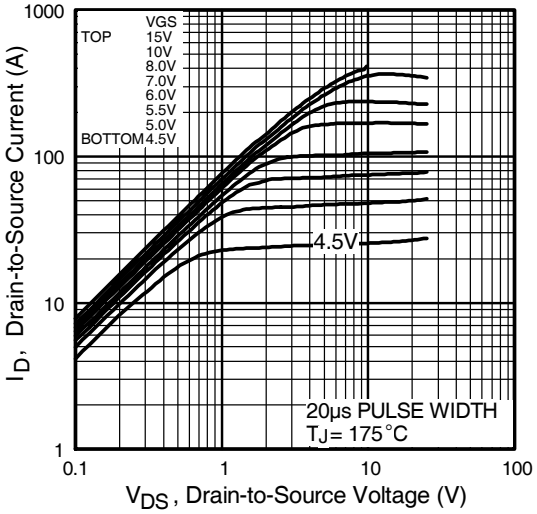


Fig 2. Typical Output Characteristics

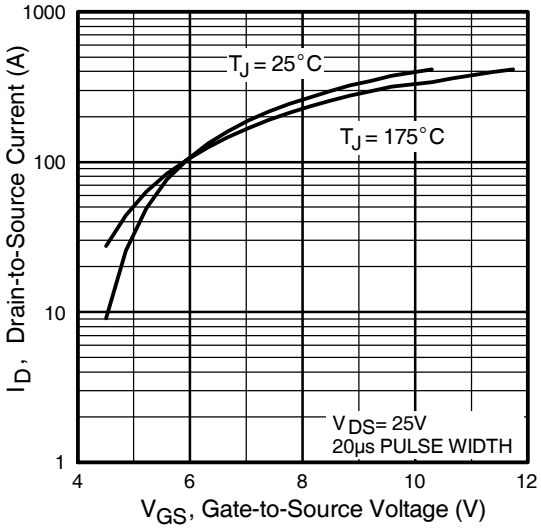


Fig 3. Typical Transfer Characteristics

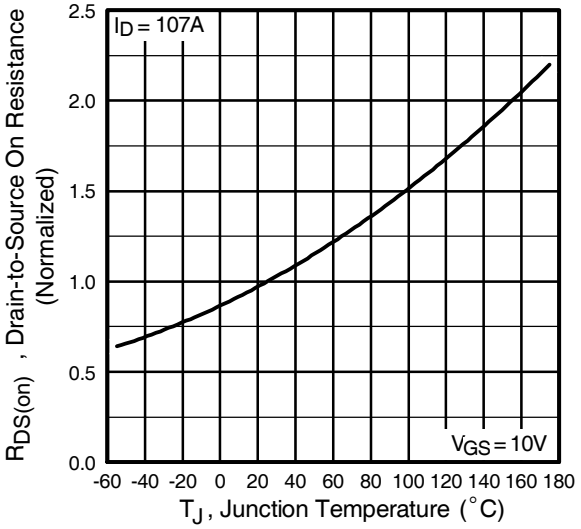


Fig 4. Normalized On-Resistance
Vs. Temperature

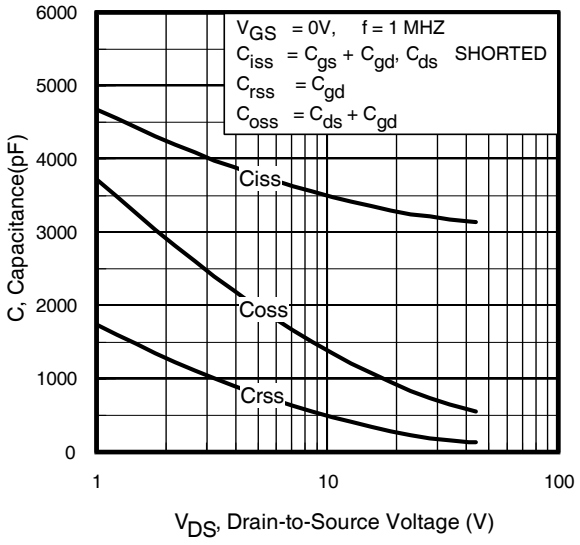


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

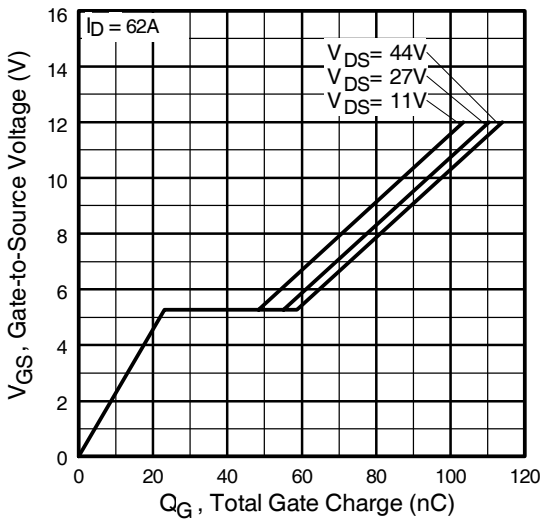


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

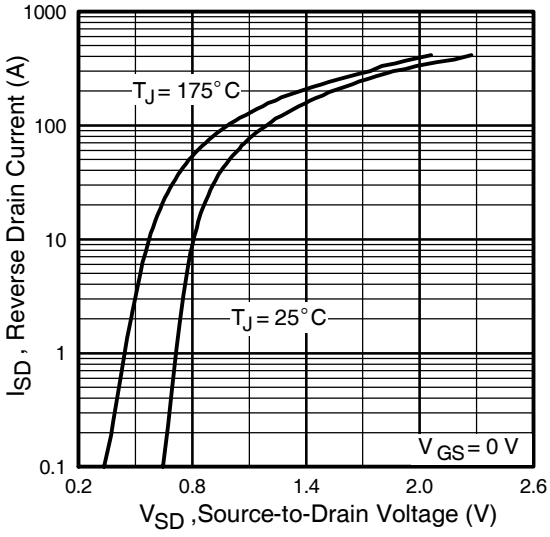


Fig 7. Typical Source-Drain Diode Forward Voltage

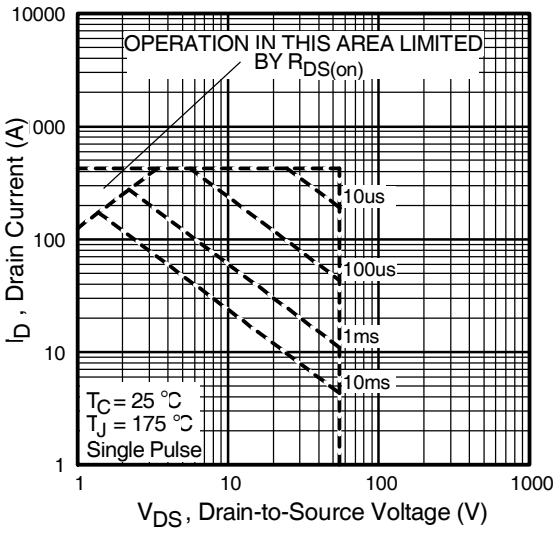


Fig 8. Maximum Safe Operating Area

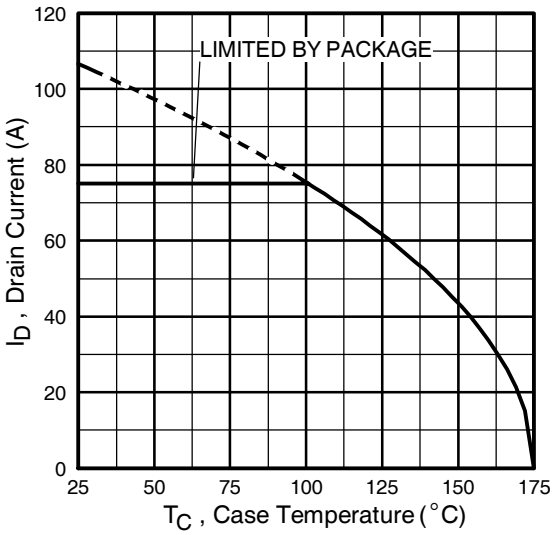


Fig 9. Maximum Drain Current Vs. Case Temperature

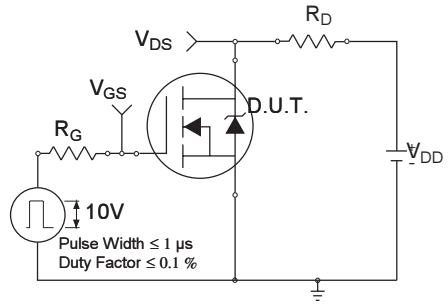


Fig 10a. Switching Time Test Circuit

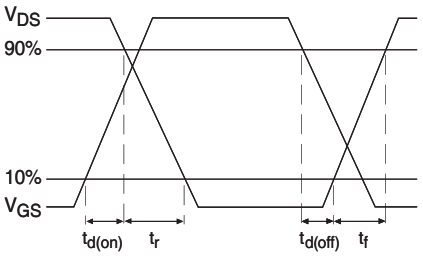


Fig 10b. Switching Time Waveforms

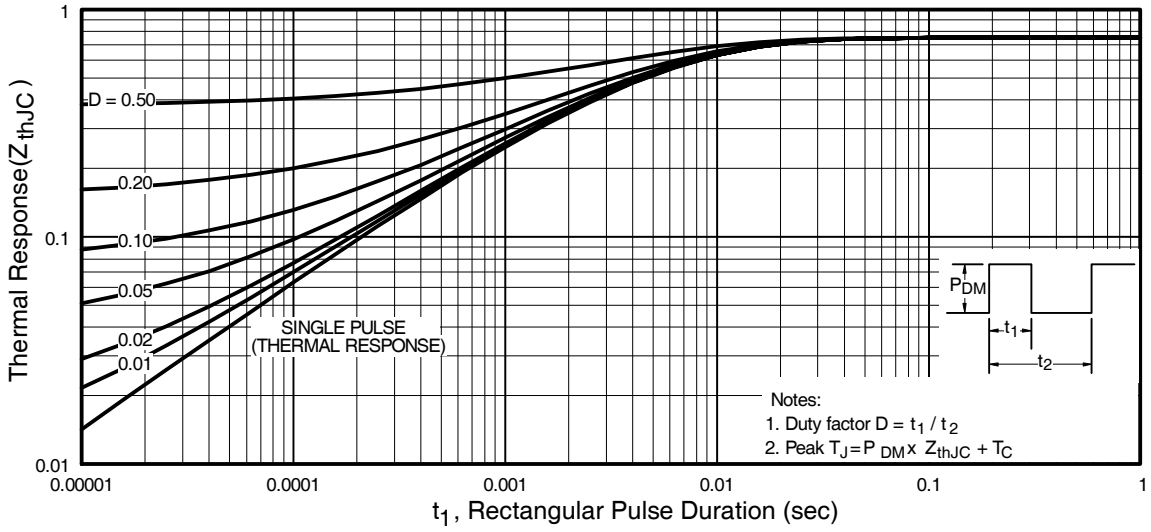


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

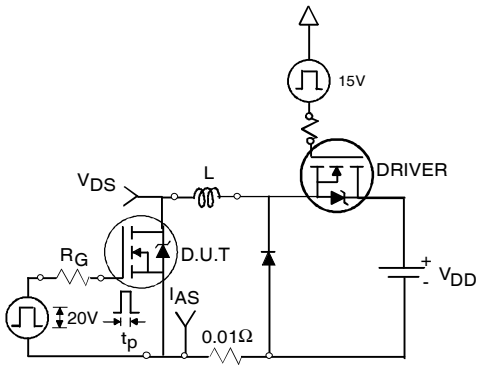


Fig 12a. Unclamped Inductive Test Circuit

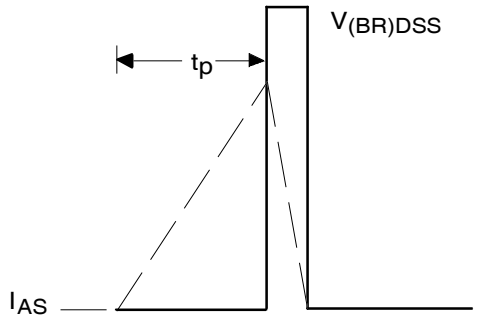


Fig 12b. Unclamped Inductive Waveforms

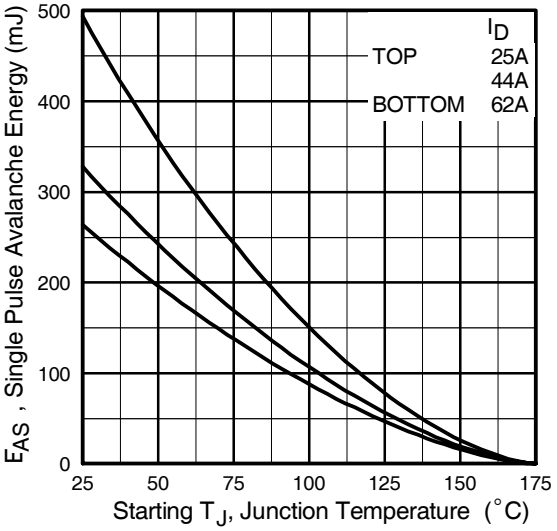


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

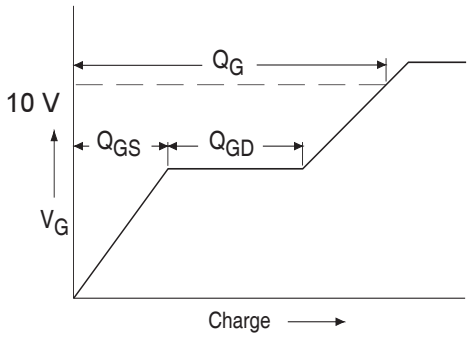


Fig 13a. Basic Gate Charge Waveform

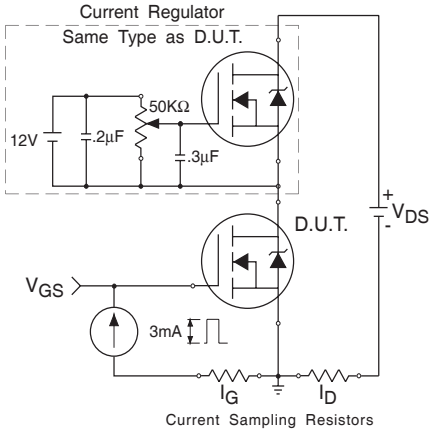
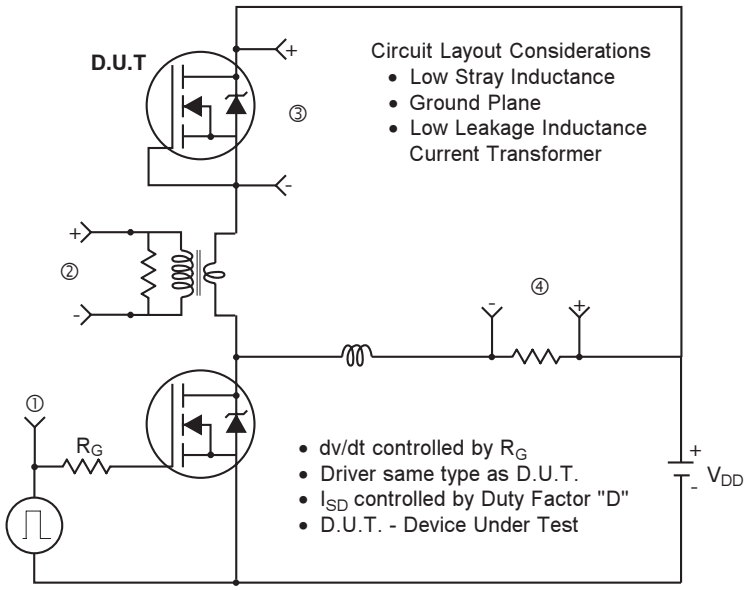
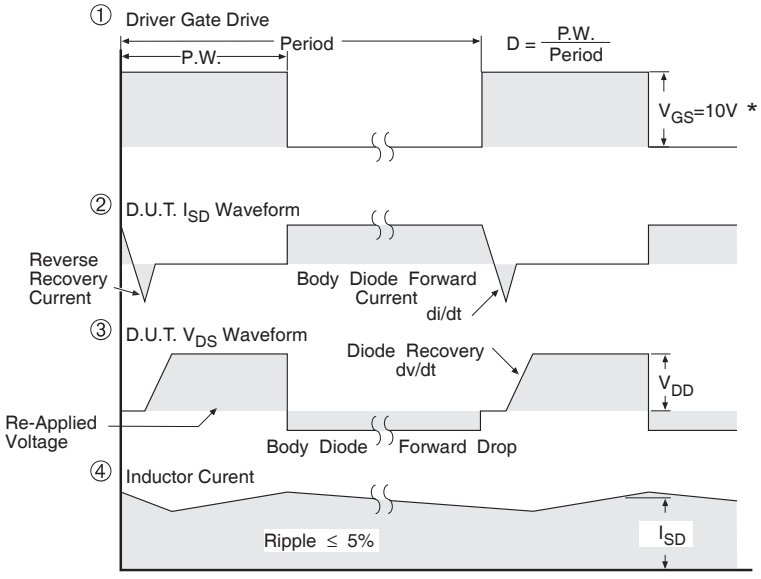


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



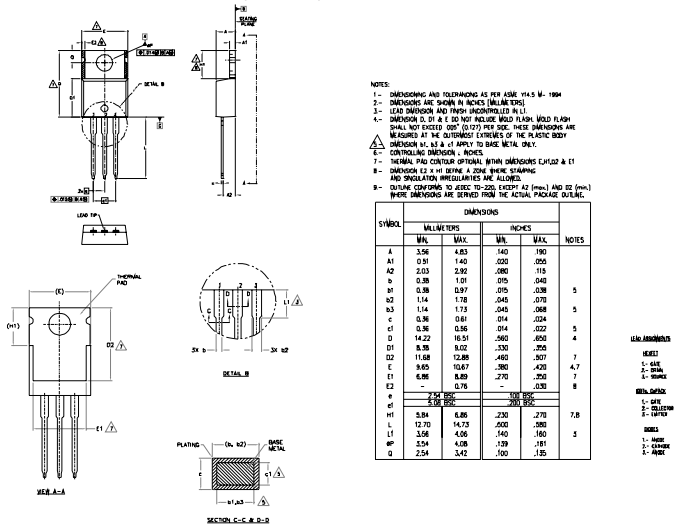


* V_{GS} = 5V for Logic Level Devices

Fig 14. For N-Channel HEXFETS

TO-220AB Package Outline

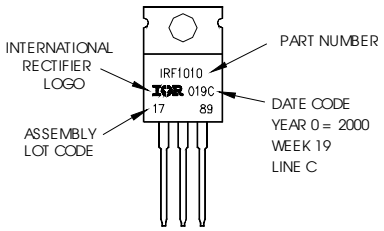
Dimensions are shown in millimeters (inches)



TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 2000
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position
indicates "Lead-Free"



TO-220AB package is not recommended for Surface Mount Application

Notes:

1. For an Automotive Qualified version of this part please see http://www.irf.com/product-info/auto/

2. For the most current drawing please refer to IR website at http://www.irf.com/package/

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

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